

/ Descriptions

KF \$) CD E GE Silicon NPN transistor in a TO-92LM Plastic Package.

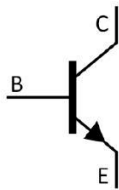
/ Features

High breakdown voltage, low output capacitance, high f_T .

/ Applications

TV video output, high voltage switching and driver stage of audio amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	70 140	120 240

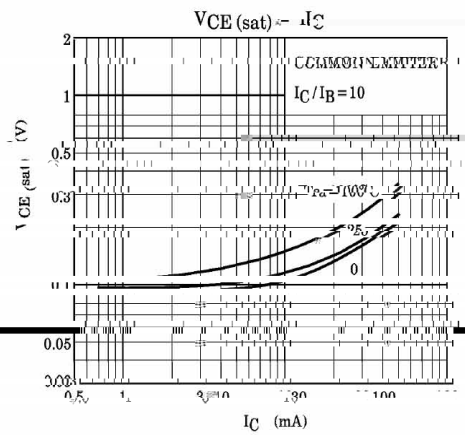
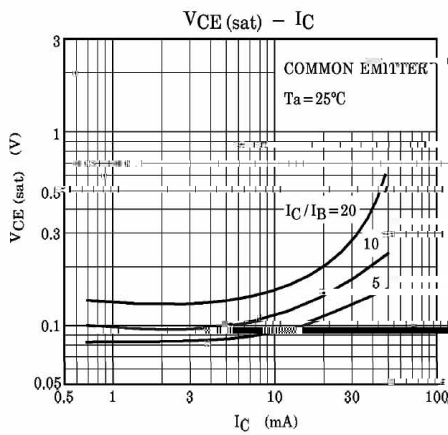
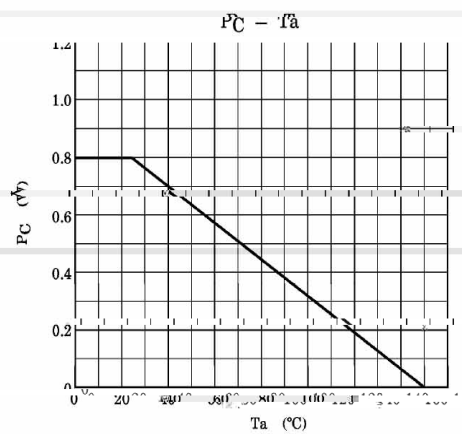
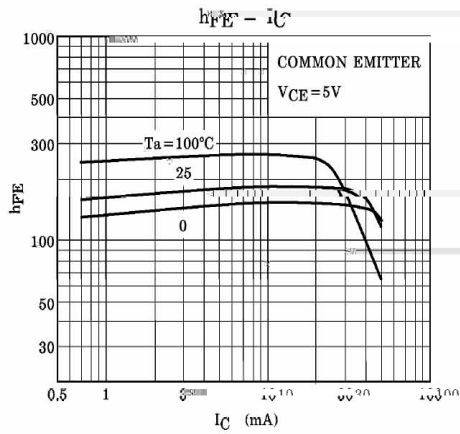
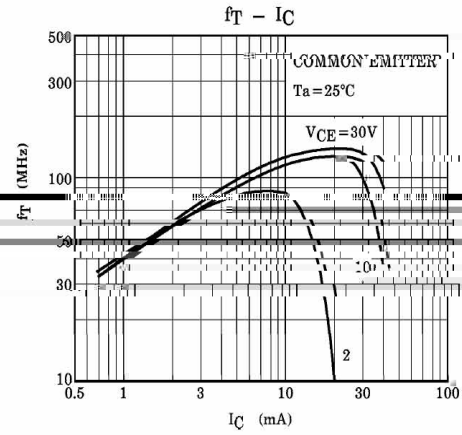
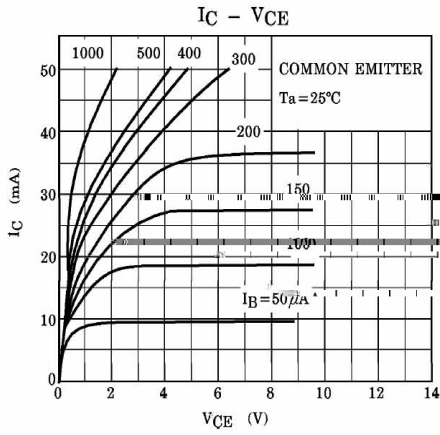
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	150	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	50	mA
Emitter Current	I_E	-50	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=200V$ $I_E=0$			0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA

DC Current Gain

h_{FE}
Typ A

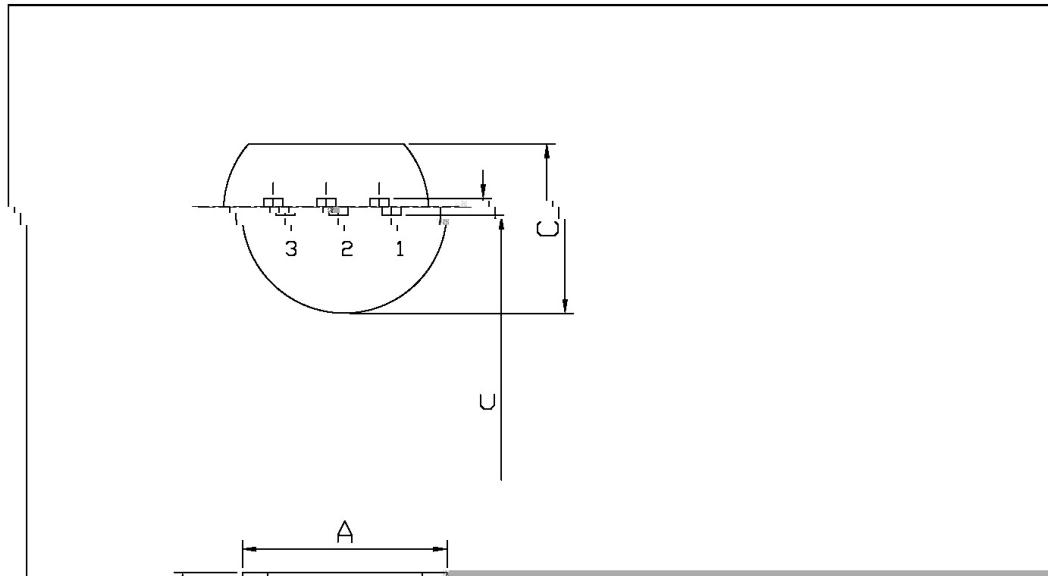
/ Electrical Characteristic Curve



/ Package Dimensions

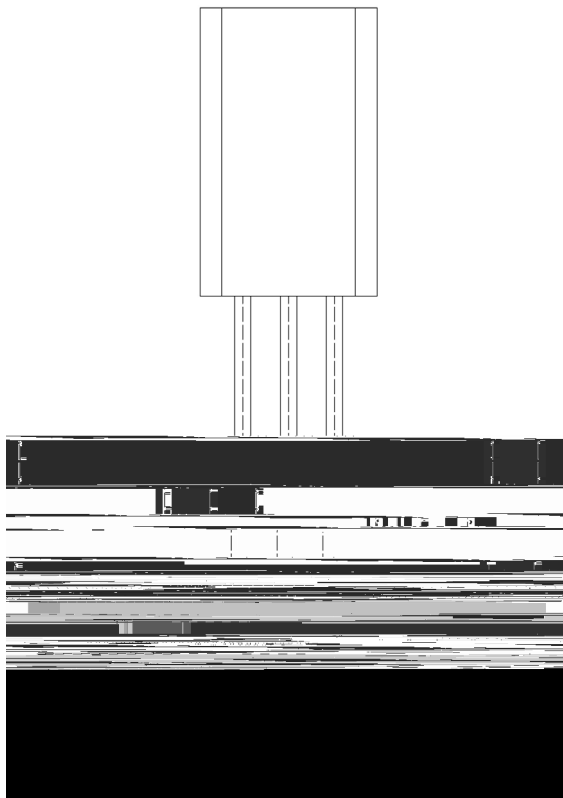
TO-92LM

Unit: mm



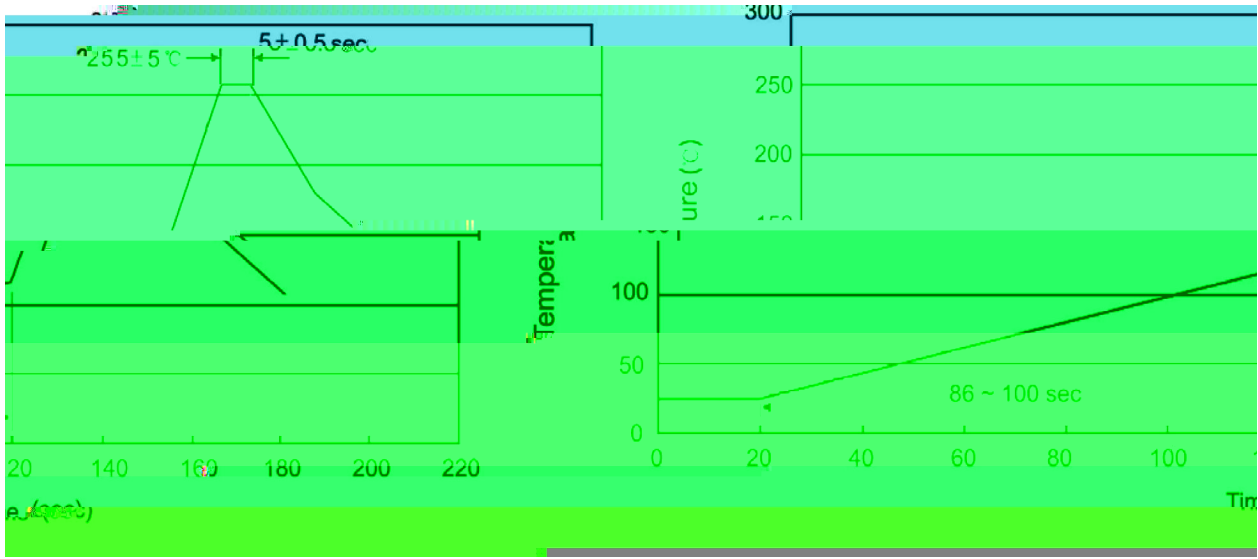
Symbol	Dimensions In Millimeters	
	Min	Max
A	4.47	5.1
C	4.47	5.1
U	1.27	1.78

/ Marking Instructions



91 1
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() / Temperature Profile for Dip Soldering(Pb-Free)



- 1 25 150 60 90sec;
- 2 255..5 5..0.5sec;
- 3 2 10 /sec.

Note:

- 1.Preheating:25~150 , Time:60~90sec.
- 2.Peak Temp.:255..5 , Duration:5..0.5sec.
- 3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270..5 10..1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK